



SEMiX 503GB126HDs



Trench IGBT Modules

SEMiX 503GB126HDs

Preliminary Data

Features

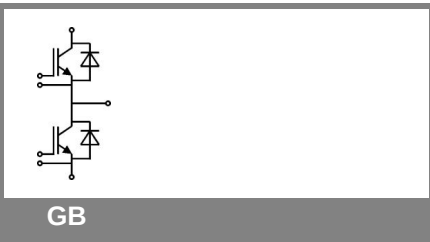
- Homogeneous Si
- Trench = Trenchgate technology
- $V_{CE(sat)}$  with positive temperature coefficient
- High short circuit capability

Typical Applications

- AC inverter drives
- UPS
- Electronic Welding

Remarks

- Case temperatur limited to  $T_C=125^{\circ}C$  max.

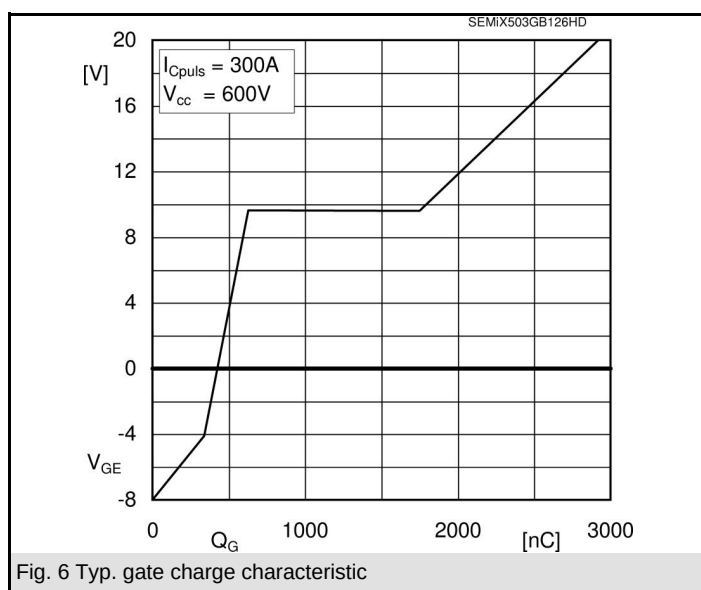
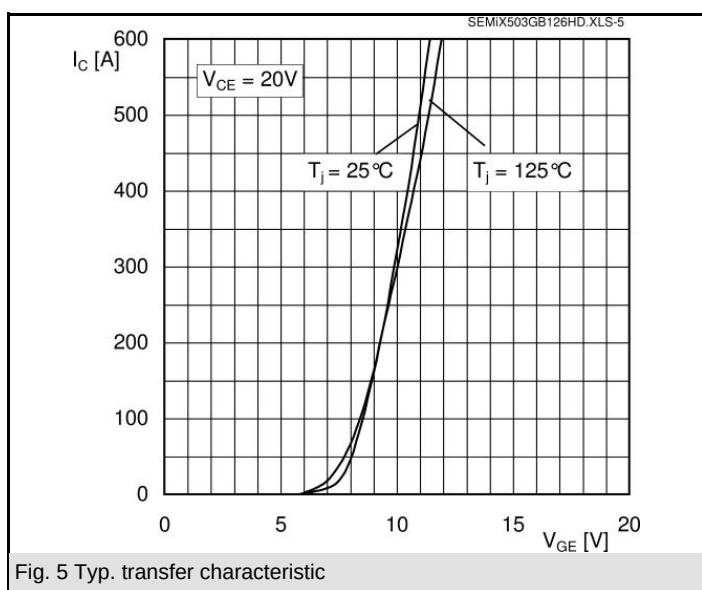
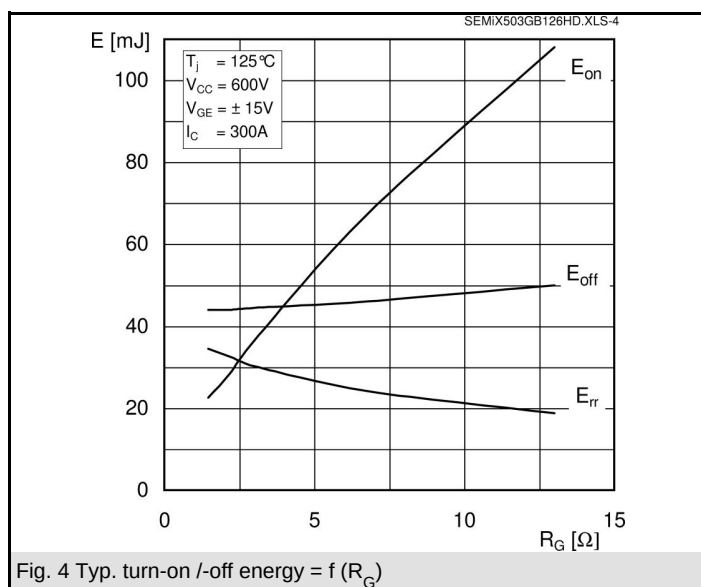
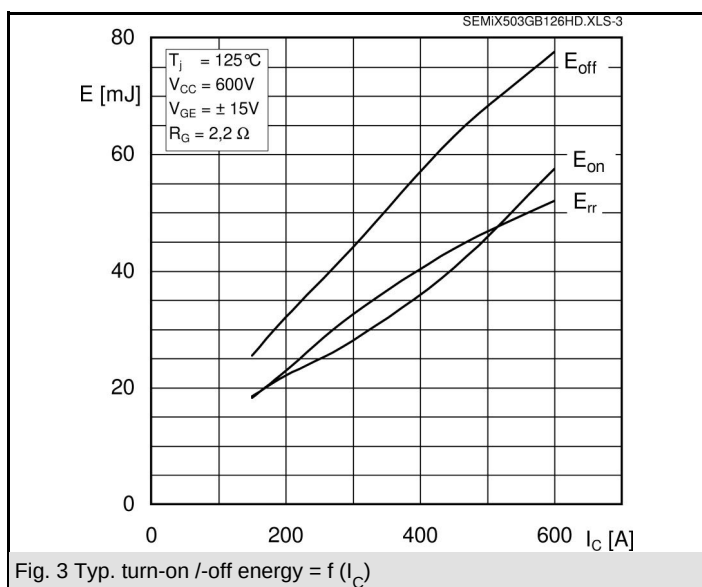
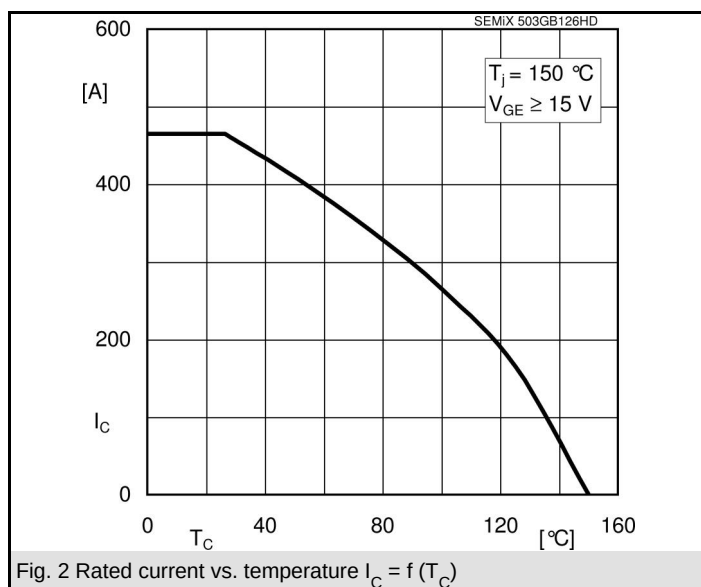
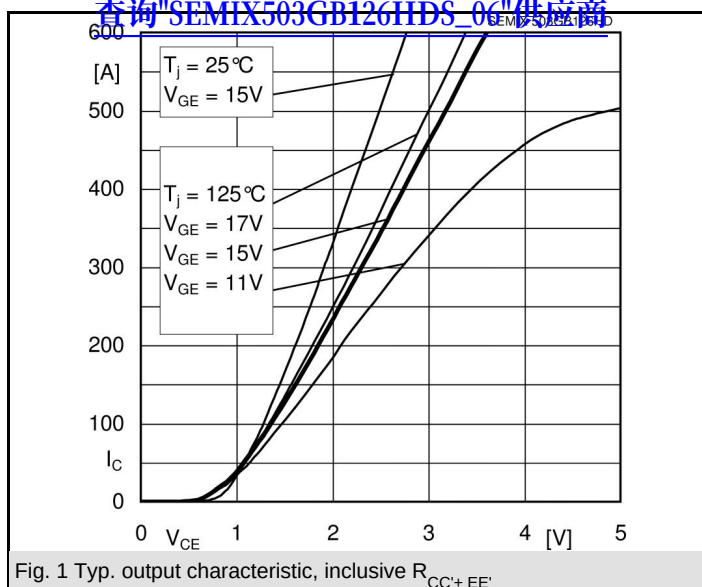


| Characteristics    |                                                                      |      |          |      |       |
|--------------------|----------------------------------------------------------------------|------|----------|------|-------|
| Symbol             | Conditions                                                           | min. | typ.     | max. | Units |
| Inverse Diode      |                                                                      |      |          |      |       |
| $V_F = V_{EC}$     | $I_{Fnom} = 300\text{ A}$ ; $V_{GE} = 0\text{ V}$                    |      |          |      |       |
|                    | $T_j = 25\text{ }^{\circ}C_{chiplev.}$                               |      | 1,6      | 1,8  | V     |
|                    | $T_j = 125\text{ }^{\circ}C_{chiplev.}$                              |      | 1,6      | 1,8  | V     |
| $V_{F0}$           |                                                                      |      |          |      |       |
|                    | $T_j = 25\text{ }^{\circ}C$                                          |      | 1        | 1,1  | V     |
|                    | $T_j = 125\text{ }^{\circ}C$                                         |      | 0,8      | 0,9  | V     |
| $r_F$              |                                                                      |      |          |      |       |
|                    | $T_j = 25\text{ }^{\circ}C$                                          |      | 2        | 2,3  | mΩ    |
|                    | $T_j = 125\text{ }^{\circ}C$                                         |      | 2,7      | 3    | mΩ    |
| $I_{RRM}$          | $I_{Fnom} = 300\text{ A}$                                            |      | 400      |      | A     |
| $Q_{rr}$           | $di/dt = 6900\text{ A}/\mu s$                                        |      | 77       |      | μC    |
| $E_{rr}$           | $V_{GE} = -15\text{ V}$ ; $V_{CC} = 600\text{ V}$                    |      | 32,5     |      | mJ    |
| $R_{th(j-c)D}$     | per diode                                                            |      |          | 0,13 | K/W   |
| Module             |                                                                      |      |          |      |       |
| $L_{CE}$           |                                                                      |      | 20       |      | nH    |
| $R_{CC'+EE'}$      | res., terminal-chip                                                  |      | 0,7      |      | mΩ    |
|                    | $T_{case} = 25\text{ }^{\circ}C$                                     |      |          |      |       |
|                    | $T_{case} = 125\text{ }^{\circ}C$                                    |      | 1        |      | mΩ    |
| $R_{th(c-s)}$      | per module                                                           |      | 0,04     |      | K/W   |
| $M_s$              | to heat sink (M5)                                                    | 3    |          | 5    | Nm    |
| $M_t$              | to terminals (M6)                                                    | 2,5  |          | 5    | Nm    |
| w                  |                                                                      |      |          | 300  | g     |
| Temperature sensor |                                                                      |      |          |      |       |
| $R_{100}$          | $T_c = 100^{\circ}C$ ( $R_{25} = 5\text{ k}\Omega$ )                 |      | 0,493±5% |      | kΩ    |
| $B_{100/125}$      | $R(T) = R_{100} \exp[B_{100/125} (1/T - 1/T_{100})]$ ;<br>$T[K]$ ; B |      | 3550±2%  |      | K     |

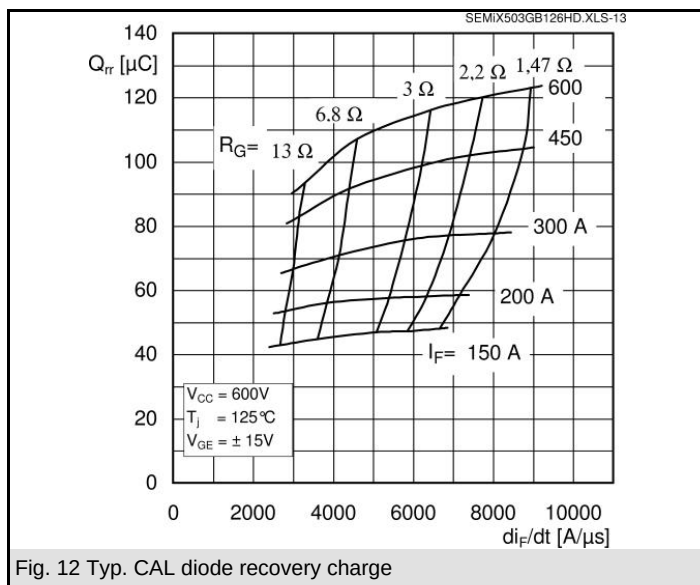
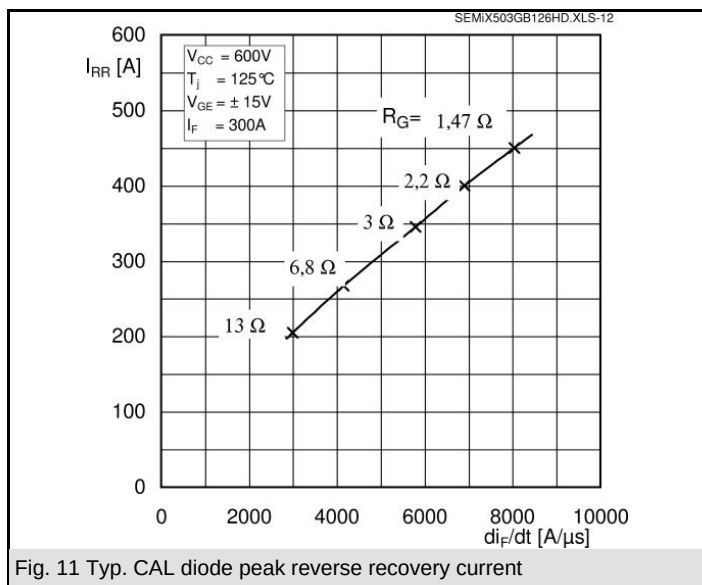
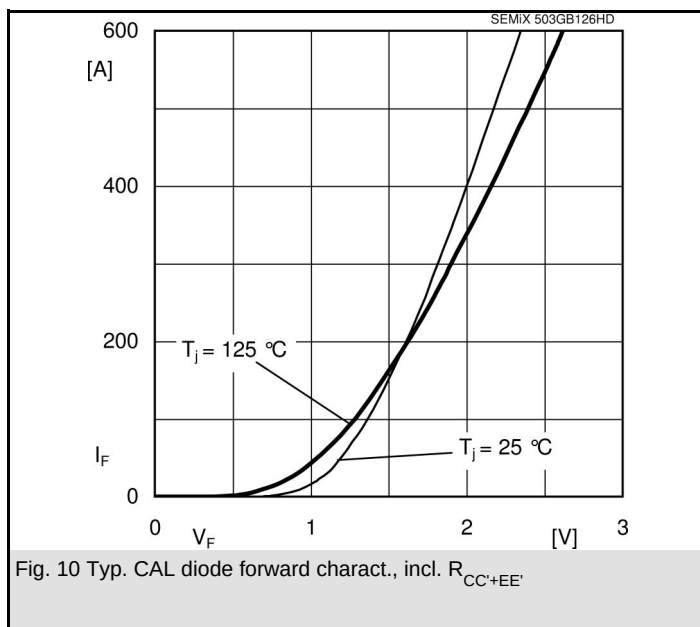
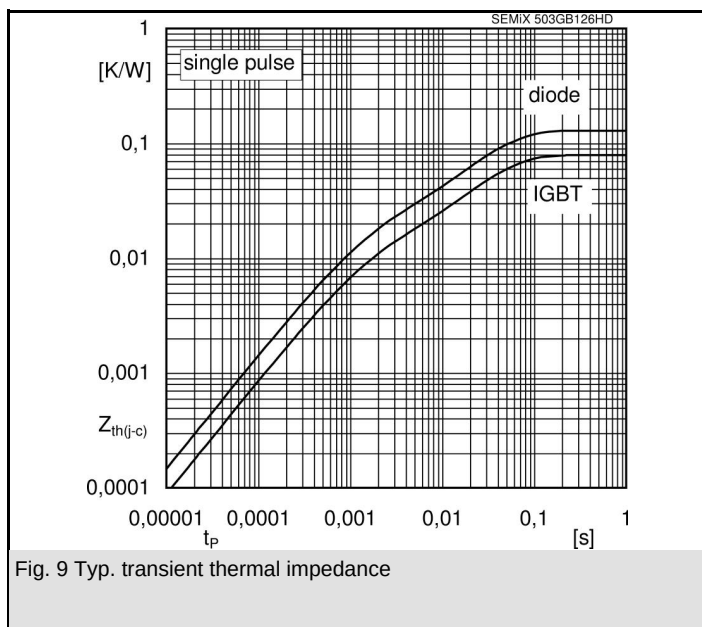
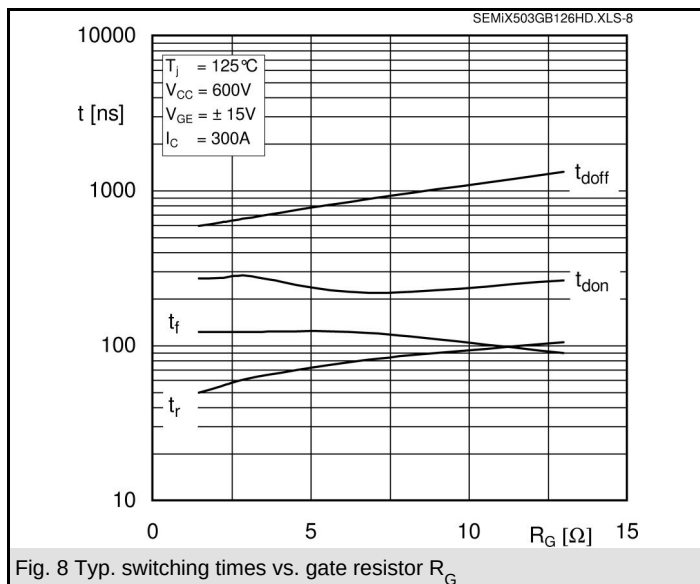
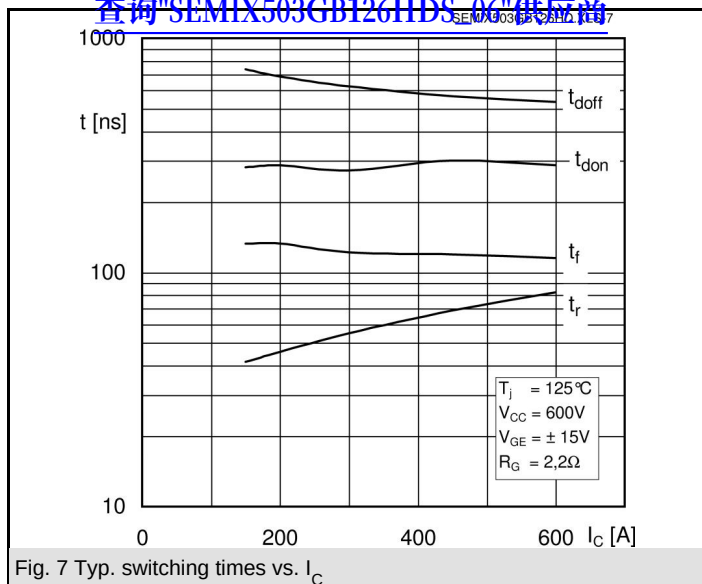
This is an electrostatic discharge sensitive device (ESDS), international standard IEC 60747-1, Chapter IX.

This technical information specifies semiconductor devices but promises no characteristics. No warranty or guarantee expressed or implied is made regarding delivery, performance or suitability.

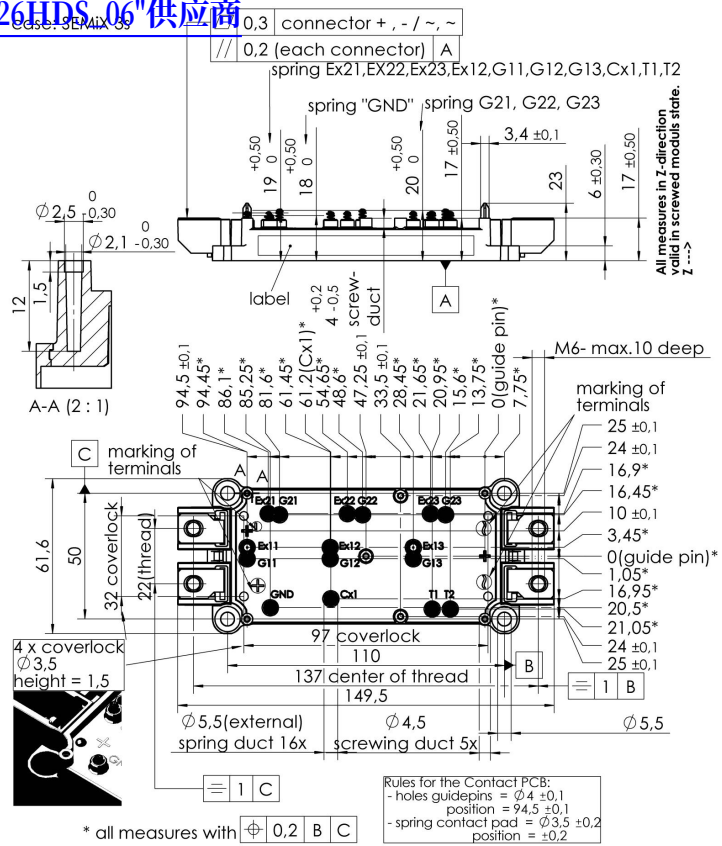
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## Case SEMiX 3s

